XN0NE92

Silicon P-channel MOSFET (FET) Silicon epitaxial planar type (SBD)

For DC-DC converter

■ Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half
- High-speed switching, low on resistance

■ Absolute Maximum Ratings $T_a = 25$ °C

					2. Cat-	
	Parameter	Symbol	Rating	Unit	3: Gate	
FET	Drain-source surrender	V _{DSS}	-12	V	■ Marking	c
	voltage				- Warking	
	Gate-source surrender	V_{GSS}	±15	V		
	voltage				Internal	C
	Drain current	I_D	-1.2	A		
	Peak drain current	I_{DP}	-3	A		
	Total power dissipation *	\mathbf{P}_{T}	600	mW		
	Channel temperature	T_{ch}	125	°C	X	þ
	Storage temperature	T _{stg}	-55 to +125	°C		1,
SBD	Reverse voltage	V_R	20	V	Labout lat	b
	Repetitive peak reverse voltage	V _{RRM}	25	V	700 ·CC)`
	Forward current (Average)	I _{F(AV)}	700	mA	r'o alli	
	Non-repetitive peak	I _{FSM}	2	A	150	
	forward surge current				.101	
Note) *:	Measuring on ceramic substrat	e at 15 mm	$1 \times 15 \text{ mm} \times 0$.6 mm	0.,,	
				N C.		
■ Elec	trical Characteristics T	$C_0 = 25^{\circ}C$	$C \pm 3^{\circ}C$	alle		
• FET		d	·x 60.	SO		
	Parameter	Symbo	\$ 00°	Condition	ns I	Μi
Drain-s	Drain-source surrender voltage		$I_{C} = 1 \text{ m/s}$	$A, V_{GS} = 0$	-	-1
Drain-s	ource cutoff current	VDSS I _{DSS}	- \ \ ·	$V, V_{GS} = 0$		_
Gate-so	ource cutoff current	I_{GSS}		$V, V_{DS} = 0$		_
G : 1	1.11.1.	***	17 10	X7 X 1		_

Parameter	Symbol	Conditions	Min	Тур	Max	Unit		
Drain-source surrender voltage	Voss	$V_{GS} = 0$	-12			V		
Drain-source cutoff current	η_{DSS}	$\dot{V}_{DS} = -10 \text{ V}, V_{GS} = 0$			-1	V		
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$			±10	V		
Gate threshold voltage	V _{th}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	- 0.4		-1.3	V		
Forward transfer admittance *	Yfs	$V_{DS} = -10 \text{ V}, I_{D} = -800 \text{ mA}$	0.8	1.1		S		
Drain-source ON resistance *	R _{DS(on)}	$V_{GS} = -4 \text{ V}, I_D = -800 \text{ mA}$		350	450	mΩ		
Turn-on time	t _{on}	$V_{DD} = -10 \text{ V}, R_L = 12.5 \Omega,$		15		ns		
Storage time	t _{stg}	$I_D = -800 \text{ mA}, V_{GS} = 0 \text{ V to } -4 \text{ V}$		10		ns		
Turn-off time	t _{off}			10		ns		

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. Observe precautions for handling. Electrostatic sensitive devices.
 - 3. *: Pulse measurement

Package

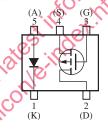
 Code Mini5-G1 (Exclusive use for XN0NE92)

Pin Name

1: Cathode 4: Source 2: Drain 5: Anode 3: Gate

■ Marking Symbol: 3F

■ Internal Connection



Publication date: April 2008 SJJ00308BED

■ Electrical Characteristics (continued) $T_a = 25$ °C ± 3 °C

• SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V _F	$I_F = 700 \text{ mA}$			0.45	V
Reverse current	I_R	$V_R = 20 \text{ V}$			200	μΑ
Terminal capacitance	C_{t}	$V_R = 0$, $f = 1$ MHz		100		pF
Reverse recovery time	t _{rr}	$I_F = I_R = 100 \text{ mA}$		7		ns
		$I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

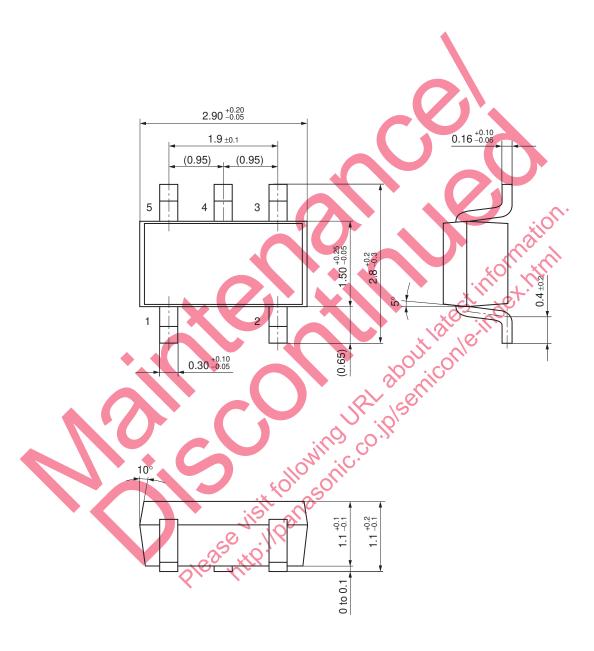
2. Schottky barrier diode is frail with static electricity, and it should be kept in safety from shock of static electricity and static electricity level.

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Unit: mm

Mini5-G1 (Exclusive use for XN0NE92)



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